TS5A22362 具有负信号功能的 0.65Ω 双通道 SPDT 模拟开关

1 特性

- 指定的先断后合开关
- 负信号处理功能：最大摆幅为从 –2.75V 至 2.75V (V_{CC} = 2.75V)
- 低导通电阻（典型值 0.65Ω）
- 低电荷注入
- 出色的导通状态电阻匹配
- 2.3V 至 5.5V 电源 (V_{CC})
- 闩锁性能超过 100mA，符合 JESD 78 II 类规范
- 静电放电 (ESD) 性能测试符合 JESD 22 标准
  - 2500V 人体放电模式（A114-B，II 类）
  - 1500V 充电器件模型 (C101)
  - 200V 机器模型 (A115-A)

2 应用

- 手机
- 个人数字助理 (PDA)
- 便携式仪表
- 音频路由
- 医疗成像

3 说明

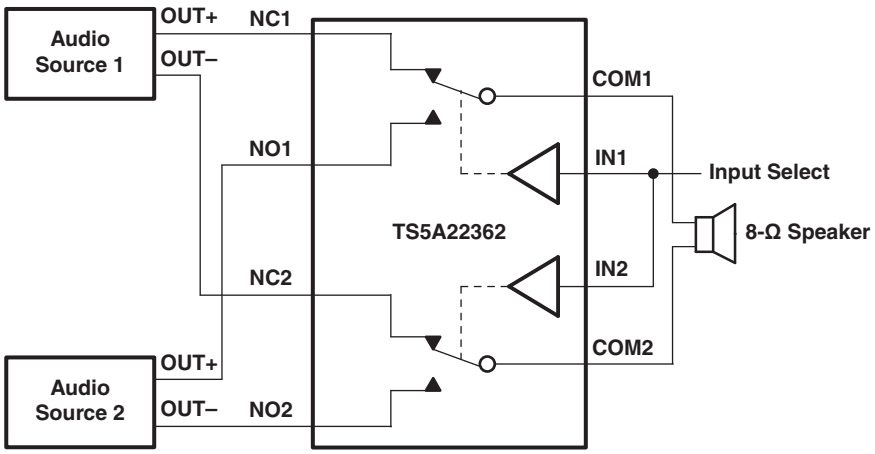
TS5A22362 是一款双向、双通道单刀双掷 (SPDT) 模拟开关，工作电压范围为 2.3V 至 5.5V。该器件 支持负信号摆幅，允许低于接地电平的信号通过开关，同时不发生失真。先断后合特性可防止信号在跨路径传输时出现失真。该器件同时拥有低导通电阻、出色的通道间导通状态电阻匹配以及最小总谐波失真 (THD) 性能，是音频应用的 理想选择。该器件还针对医疗成像应用提供了一种非磁性封装，即 3.00mm × 3.00mm DRC 封装。

器件信息(1)

器件型号	封装	封装尺寸（标称值）
TS5A22362	VSON (10)	3.00mm × 3.00mm
	DSBGA (10)	1.86mm x 1.36mm
	VSSOP (10)	3.00mm × 3.00mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。

典型应用原理图



目录

4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

Changes from Revision D (March 2018) to Revision E **Page**

- Changed the YZP Package view From: Top View To: Bottom View ... 3

Changes from Revision C (June 2017) to Revision D **Page**

- Changed the YZP Package From: Laser Marketing View and Bump View To: Top View ... 3
- Changed the Q_C TYP value From: 10 pC To: 150 pC in the *Electrical Characteristics for 5-V Supply* table ... 8

Changes from Revision B (September 2015) to Revision C **Page**

- Changed the V_{IN} MAX value From: V_{CC} To: 5.5 V in the *Recommended Operating Conditions* table ... 4

Changes from Revision A (August 2015) to Revision B **Page**

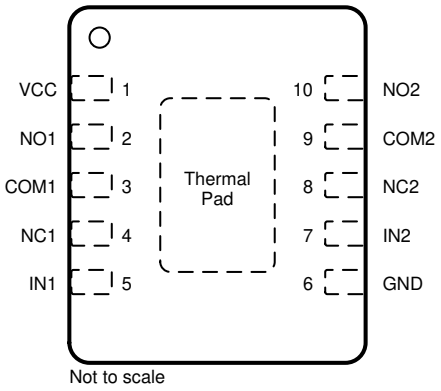
- Changed C_L TEST CONDITION value for all THD PARAMETERs from 15 pf to 35 pf. ... 6

Changes from Original (June 2015) to Revision A **Page**

- Changed the Functional Block Diagram. ... 15

5 Pin Configuration and Functions

DRC Package
10-Pin VSON
Top View



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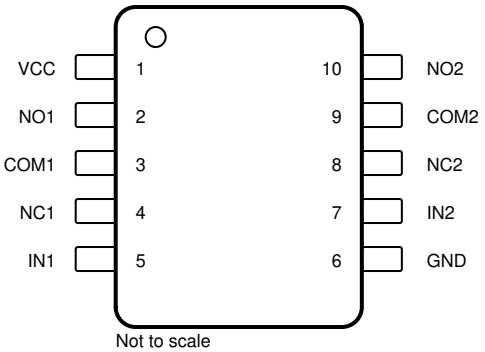
The exposed center pad, if used, must be connected as a secondary GND or left electrically open.

DGS Package
10-Pin VSSOP
Top View



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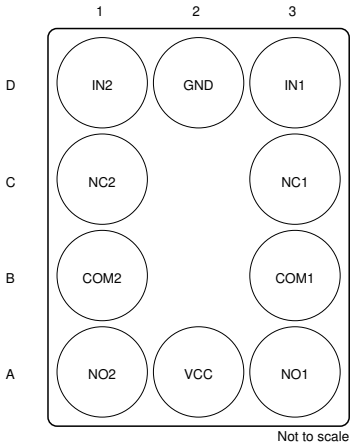
YZP Package
10-Pin DSBGA
Bottom View



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Pin Functions

PIN				TYPE	DESCRIPTION
NAME	VSON	VSSOP	DSBGA		
VCC	1	1	A2	—	Power Supply
NO1	2	2	A3	I/O	Normally Open (NO) signal path, Switch 1
COM1	3	3	B3	I/O	Common signal path, Switch 1
NC1	4	4	C3	I/O	Normally Closed (NC) signal path, Switch 1
IN1	5	5	D3	I	Digital control pin , Switch 1
GND	6	6	D2	—	Ground
IN2	7	7	D1	I	Digital control pin, Switch 2
NC2	8	8	C1	I/O	Normally Closed (NC) signal path, Switch 2
COM2	9	9	B1	I/O	Common signal path, Switch 2
NO2	10	10	A1	I/O	Normally Open (NO) signal Path, Switch 2

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted) (1)

			MIN	MAX	UNIT
V_{CC} (2)	Supply voltage (3)		–0.5	6	V
V_{NC} V_{NO} V_{COM}	Analog voltage (3) (4) (5)		V_{CC} – 6	V_{CC} + 0.5	V
$I_{I/OK}$	Analog port diode current	V_{NC}, V_{NO}, V_{COM} < 0 or V_{NC}, V_{NO}, V_{COM} > V_{CC}	–50	50	mA
I_{NC} I_{NO} I_{COM}	ON-state switch current	V_{NC}, V_{NO}, V_{COM} = 0 to V_{CC}	–150	150	mA
	ON-state peak switch current (6)		–300	300	
I_{NC} (3) (7) (8) I_{NO} (3) (7) (8) I_{COM} (3) (7) (8)	ON-state switch current	V_{NC}, V_{NO}, V_{COM} = 0 to V_{CC}	–350	350	mA
	ON-state peak switch current (6)		–500	500	
V_I	Digital input voltage		–0.5	6.5	V
I_{IK}	Digital input clamp current (3) (4)	V_I < 0	–50	50	mA
I_{CC} I_{GND}	Continuous current through V_{CC}or GND		–100	100	mA
T_{stg}	Storage temperature		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* . Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum
(3) All voltages are with respect to ground, unless otherwise specified.
(4) The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
(5) This value is limited to 5.5 V maximum.
(6) Pulse at 1-ms duration < 10% duty cycle.
(7) V_{CC} = 3.0 V to 5.0 V, T_A = –40°C to 85°C.
(8) For YZP package only.

6.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$ Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	±2500	V
	Charged-device model (CDM), per JEDEC specification JESD22-C101 (2)	±1500	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V_{CC}	Supply voltage	2.3	5.5	V
V_{NC} V_{NO} V_{COM}	Signal path voltage	V_{CC} – 5.5	V_{CC}	V
V_{IN}	Digital control	GND	5.5	V

6.4 Thermal Information

THERMAL METRIC (1)		TS5A22362			UNIT
		DGS (VSSOP)	DRC (VSON)	YZP (DSBGA)	
		10 PINS	10 PINS	10 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	163.3	44.3	90.9	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	56.4	70.1	0.3	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	83.1	19.3	8.3	°C/W
ψ_{JT}	Junction-to-top characterization parameter	6.8	2.0	3.2	°C/W
ψ_{JB}	Junction-to-board characterization parameter	81.8	19.4	8.3	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

6.5 Electrical Characteristics for 2.5-V Supply

V_{CC} = 2.3 V to 2.7 V, T_A = –40°C to 85°C (unless otherwise noted) (1)

PARAMETER		TEST CONDITIONS		T_A	V_{CC}	MIN	TYP	MAX	UNIT
Analog Switch									
V_{COM}, V_{NO}, V_{NC}	Analog signal range					V_{CC} – 5.5		V_{CC}	V
R_{on}	ON-state resistance	V_{NC} or V_{NO} = V_{CC}, 1.5 V, V_{CC} – 5.5 V I_{COM} = –100 mA,	COM to NO or NC, see Figure 13	25°C	2.7 V		0.65	0.94	Ω
				Full				1.3	
ΔR_{on}	ON-state resistance match between channels	V_{NC} or V_{NO} = 1.5 V, I_{COM} = –100 mA,	COM to NO or NC, see Figure 13	25°C	2.7 V		0.023	0.11	Ω
				Full				0.15	
$R_{on(flat)}$	ON-state resistance flatness	V_{NC} or V_{NO} = V_{CC}, 1.5 V, V_{CC} – 5.5 V I_{COM} = –100 mA,	COM to NO or NC, see Figure 13	25°C	2.7 V		0.18	0.46	Ω
				Full				0.5	
$I_{NC(OFF)}$, $I_{NO(OFF)}$	NC, NO OFF leakage current	V_{NC} = 2.25 V, V_{CC} – 5.5 V V_{COM} = V_{CC} – 5.5 V, 2.25 V V_{NO} = Open COM to NO or V_{NO} = 2.25 V, V_{CC} – 5.5 V, V_{COM} = V_{CC} – 5.5 V, 2.25 V V_{NC} = Open COM to NC	See Figure 14	25°C	2.7	–50		50	nA
				Full		–375		375	
$I_{COM(ON)}$	COM ON leakage current	V_{NC} and V_{NO} = Floating, V_{COM} = V_{CC},V_{CC} – 5.5 V	See Figure 15	25°C	2.7 V	–50		50	nA
				Full		–375		375	
Digital Control Inputs (IN) (2)									
V_{IH}	Input logic high			Full		1.4		5.5	V
V_{IL}	Input logic low							0.6	
I_{IH}, I_{IL}	Input leakage current	V_{IN} = V_{CC} or 0		25°C	2.7 V	–250		250	nA
				Full		–250		250	
Dynamic									
t_{ON}	Turnon time	V_{COM} = V_{CC}, R_L = 300 Ω,	C_L = 35 pF, see Figure 17	25°C	2.5 V		44	80	ns
				Full	2.3 V to 2.7 V			120	
t_{OFF}	Turnoff time	V_{COM} = V_{CC}, R_L = 300 Ω,	C_L = 35 pF, see Figure 17	25°C	2.5 V		22	70	ns
				Full	2.3 V to 2.7 V			70	
t_{BBM}	Break-before-make time	See Figure 18		25°C	2.5 V	1	7		ns
Q_C	Charge injection	V_{GEN} = 0, R_{GEN} = 0,	C_L = 1 nF, see Figure 22	25°C	2.5 V		150		pC
$C_{NC(OFF)}$, $C_{NO(OFF)}$	NC, NO OFF capacitance	V_{NC} or V_{NO} = V_{CC} or GND,	See Figure 16	25°C	2.5 V		70		pF

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum
(2) All unused digital inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, SCBA004.

Electrical Characteristics for 2.5-V Supply (continued)

V_{CC} = 2.3 V to 2.7 V, T_A = –40°C to 85°C (unless otherwise noted) (1)

PARAMETER		TEST CONDITIONS		T_A	V_{CC}	MIN	TYP	MAX	UNIT
$C_{COM(ON)}$	NC, NO, COM ON capacitance	V_{COM} = V_{CC} or GND, Switch ON, f = 10 MHz	See Figure 16	25°C	2.5 V		370		pF
C_I	Digital input capacitance	V_I = V_{CC} or GND	See Figure 16	25°C	2.5 V		2.6		pF
BW	Bandwidth	R_L = 50 Ω, –3 dB	See Figure 18	25°C	2.5 V		17		MHz
O_{ISO}	OFF isolation	R_L = 50 Ω	f = 100 kHz, see Figure 20	25°C	2.5 V		–66		dB
X_{TALK}	Crosstalk	R_L = 50 Ω	f = 100 kHz, see Figure 21	25°C	2.5 V		–75		dB
THD	Total harmonic distortion	R_L = 600 Ω, C_L = 35 pF	f = 20 Hz to 20 kHz, see Figure 23	25°C	2.5 V		0.01%		
Supply									
I_{CC}	Positive supply current	V_{COM} and V_{IN} = V_{CC} or GND, V_{NC} and V_{NO} = Floating		25°C	2.7 V		0.2	1.1	µA
				Full				1.3	
I_{CC}	Positive supply current	V_{COM} = V_{CC} – 5.5 V, V_{IN} = V_{CC} or GND, V_{NC} and V_{NO} = Floating		Full	2.7 V			3.3	µA

6.6 Electrical Characteristics for 3.3-V Supply

V_{CC} = 3 V to 3.6 V, T_A = –40°C to 85°C (unless otherwise noted) (1)

PARAMETER		TEST CONDITIONS		T_A	V_{CC}	MIN	TYP	MAX	UNIT
ANALOG SWITCH									
V_{COM}, V_{NO}, V_{NC}	Analog signal range					V_{CC} – 5.5		V_{CC}	V
R_{on}	ON-state resistance	V_{NC} or V_{NO} ≤ V_{CC}, 1.5 V, V_{CC} – 5.5 V, I_{COM} = –100 mA	COM to NO or NC, see Figure 13	25°C	3 V		0.61	0.87	Ω
				Full				0.97	
ΔR_{on}	ON-state resistance match between channels	V_{NC} or V_{NO} = 1.5 V, I_{COM} = –100 mA,	COM to NO or NC, see Figure 13	25°C	3 V		0.024	0.13	Ω
				Full				0.13	
$R_{on(flat)}$	ON-state resistance flatness	V_{NC} or V_{NO} ≤ V_{CC}, 1.5 V, V_{CC} – 5.5 V, I_{COM} = –100 mA	COM to NO or NC, see Figure 13	25°C	3 V		0.12	0.46	Ω
				Full				0.5	
$I_{NC(OFF)}$, $I_{NO(OFF)}$	NC, NO OFF leakage current	V_{NC} = 3 V, V_{CC} – 5.5 V V_{COM} = V_{CC} – 5.5 V, 3 V V_{NO} = Open COM to NO or V_{NO} = 3 V, V_{CC} – 5.5 V, V_{COM} = V_{CC} – 5.5 V, 3 V V_{NC} = Open COM to NC	See Figure 14	25°C	3.6 V	–50		50	nA
				Full		–375		375	
$I_{COM(ON)}$	COM ON leakage current	V_{NC} and V_{NO} = Floating, V_{COM} = V_{CC},V_{CC} – 5.5 V	COM to NO or NC, see Figure 15	25°C	3.6 V	–50		50	nA
				Full		–375		375	
DIGITAL CONTROL INPUTS (IN) (2)									
V_{IH}	Input logic high			Full		1.4		5.5	V
V_{IL}	Input logic low							0.8	
I_{IH}, I_{IL}	Input leakage current	V_{IN} = V_{CC} or 0		25°C	3.6 V	–250		250	nA
				Full		–250		250	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum
(2) All unused digital inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

Electrical Characteristics for 3.3-V Supply (continued)

V_{CC} = 3 V to 3.6 V, T_A = –40°C to 85°C (unless otherwise noted) (1)

PARAMETER		TEST CONDITIONS		T_A	V_{CC}	MIN	TYP	MAX	UNIT
DYNAMIC									
t_{ON}	Turnon time	V_{COM} = V_{CC}, R_L = 300 Ω	C_L = 35 pF, see Figure 17	25°C	3.3 V		34	80	ns
				Full	3 V to 3.6 V			120	
t_{OFF}	Turnoff time	V_{COM} = V_{CC}, R_L = 300 Ω	C_L = 35 pF, see Figure 17	25°C	3.3 V		19	70	ns
				Full	3 V to 3.6 V			70	
t_{BBM}	Break-before-make time	See Figure 18		25°C	3.3 V	1	7		ns
Q_C	Charge injection	V_{GEN} = 0, R_{GEN} = 0	C_L = 1 nF, see Figure 22	25°C	3.3 V		150		pC
$C_{NC(OFF)}$, $C_{NO(OFF)}$	NC, NO OFF capacitance	V_{NC} or V_{NO} = V_{CC} or V_{CC} – 5.5 V	See Figure 16	25°C	3.3 V		70		pF
$C_{COM(ON)}$	NC, NO, COM ON capacitance	V_{COM} = V_{CC} or GND, f = 10 MHz	See Figure 16	25°C	3.3 V		370		pF
C_I	Digital input capacitance	V_I = V_{CC} or GND	See Figure 16	25°C	3.3 V		2.6		pF
BW	Bandwidth	R_L = 50 Ω, –3 dB	Switch ON, see Figure 18	25°C	3.3 V		17.5		MHz
O_{ISO}	OFF isolation	R_L = 50 Ω	f = 100 kHz, see Figure 20	25°C	3.3 V		–68		dB
X_{TALK}	Crosstalk	R_L = 50 Ω	f = 100 kHz, see Figure 21	25°C	3.3 V		–76		dB
THD	Total harmonic distortion	R_L = 600 Ω, C_L = 35 pF	f = 20 Hz to 20 kHz, see Figure 23	25°C	3.3 V		0.008%		
SUPPLY									
I_{CC}	Positive supply current	V_{COM} and V_{IN} = V_{CC} or GND, V_{NC} and V_{NO} = Floating		25°C	3.6 V		0.1	1.2	µA
				Full				1.3	
		V_{COM} = V_{CC} – 5.5 V, V_{IN} = V_{CC} or GND, V_{NC} and V_{NO} = Floating		Full	3.6 V			3.4	µA

6.7 Electrical Characteristics for 5-V Supply

V_{CC} = 4.5 V to 5.5 V, T_A = –40°C to 85°C (unless otherwise noted) (1)

PARAMETER		TEST CONDITIONS		T_A	V_{CC}	MIN	TYP	MAX	UNIT
ANALOG SWITCH									
V_{COM}, V_{NO}, V_{NC}	Analog signal range					V_{CC} – 5.5		V_{CC}	V
R_{on}	ON-state resistance	V_{NC} or V_{NO} = V_{CC}, 1.6 V, V_{CC} = –5.5 V, I_{COM} = –100 mA	COM to NO or NC, see Figure 13	25°C	4.5 V		0.52	0.74	Ω
				Full				0.83	
ΔR_{on}	ON-state resistance match between channels	V_{NC} or V_{NO} = 1.6 V, I_{COM} = –100 mA	COM to NO or NC, see Figure 13	25°C	4.5 V		0.04	0.23	Ω
				Full				0.30	
$R_{on(flat)}$	ON-state resistance flatness	V_{NC} or V_{NO} = V_{CC}, 1.6 V, V_{CC} = –5.5 V, I_{COM} = –100 mA	COM to NO or NC, see Figure 13	25°C	4.5 V		0.076	0.46	Ω
				Full				0.5	
$I_{NC(OFF)}$, $I_{NO(OFF)}$	NC, NO OFF leakage current	V_{NC} = 4.5 V, V_{CC} – 5.5 V, V_{COM} = V_{CC} – 5.5 V, 4.5 V, V_{NO} = Open, COM to NO or V_{NO} = 4.5 V, V_{CC} – 5.5 V, V_{COM} = V_{CC} – 5.5 V, 4.5 V, V_{NC} = Open, COM to NC	See Figure 14	25°C	5.5 V	–50		50	nA
				Full		–375		375	
$I_{COM(ON)}$	COM ON leakage current	V_{NC} and V_{NO} = Floating, V_{COM} = V_{CC}, V_{CC} – 5.5 V	See Figure 15	25°C	5.5 V	–50		50	nA
				Full		–375		375	

(1) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum

Electrical Characteristics for 5-V Supply (continued)

V_{CC} = 4.5 V to 5.5 V, T_A = –40°C to 85°C (unless otherwise noted) (1)

PARAMETER		TEST CONDITIONS		T_A	V_{CC}	MIN	TYP	MAX	UNIT
DIGITAL CONTROL INPUTS (IN) (2)									
V_{IH}	Input logic high			Full		2.4		5.5	V
V_{IL}	Input logic low							0.8	
I_{IH}, I_{IL}	Input leakage current	V_{IN} = V_{CC} or 0		25°C	5.5 V	–250		250	nA
				Full		–250		250	
DYNAMIC									
t_{ON}	Turnon time	V_{COM} = V_{CC}, R_L = 300 Ω	C_L = 35 pF, see Figure 17	25°C	5 V		27	80	ns
				Full	4.5 V to 5.5 V			80	
t_{OFF}	Turnoff time	V_{COM} = V_{CC}, R_L = 300 Ω	C_L = 35 pF, see Figure 17	25°C	5 V		13	70	ns
				Full	4.5 V to 5.5 V			70	
t_{BBM}	Break-before-make time	V_{NC} = V_{NO} = V_{CC}/2 R_L = 300 Ω	C_L = 35 pF, see Figure 18	25°C	5 V	1	3.5		ns
Q_C	Charge injection	V_{GEN} = 0, R_{GEN} = 0	C_L = 1 nF, see Figure 22	25°C	5 V		150		pC
$C_{NC(OFF)}$, $C_{NO(OFF)}$	NC, NO OFF capacitance	V_{NC} or V_{NO} = V_{CC} or V_{CC} – 5.5 V	See Figure 16	25°C	5 V		70		pF
$C_{COM(ON)}$	NC, NO, COM ON capacitance	V_{COM} = V_{CC} or GND,	See Figure 16	25°C	5 V		370		pF
C_I	Digital input capacitance	V_I = V_{CC} or GND	See Figure 16	25°C	5 V		2.6		pF
BW	Bandwidth	R_L = 50 Ω	See Figure 18	25°C	5 V		18.3		MHz
O_{ISO}	OFF isolation	R_L = 50 Ω	f = 100 kHz, see Figure 20	25°C	5 V		–70		dB
X_{TALK}	Crosstalk	R_L = 50 Ω	f = 100 kHz, see Figure 21	25°C	5 V		–78		dB
THD	Total harmonic distortion	R_L = 600 Ω, C_L = 35 pF	f = 20 Hz to 20 kHz, see Figure 23	25°C	5 V		0.009%		
SUPPLY									
I_{CC}	Positive supply current	V_{COM} and V_{IN} = V_{CC} or GND, V_{NC} and V_{NO} = Floating		25°C	5.5 V		0.2	1.3	μA
				Full				3.5	
		V_{COM} = V_{CC} – 5.5 V, V_{IN} = V_{CC} or GND, V_{NC} and V_{NO} = Floating		Full				5	

(2) All unused digital inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, SCBA004.

6.8 Typical Characteristics

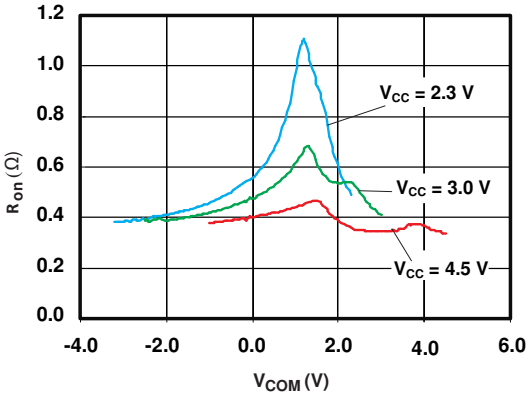


Figure 1. R_{on} vs V_{COM}

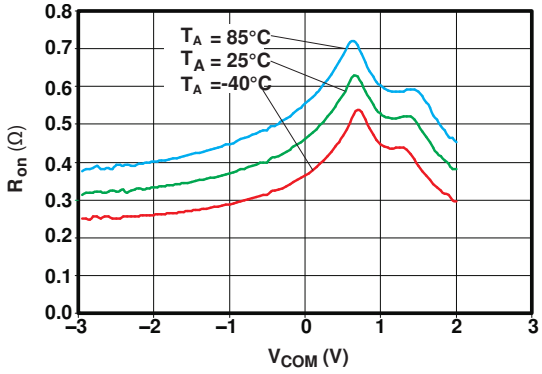


Figure 2. R_{on} vs V_{COM} (V_{CC} = 2.7 V)

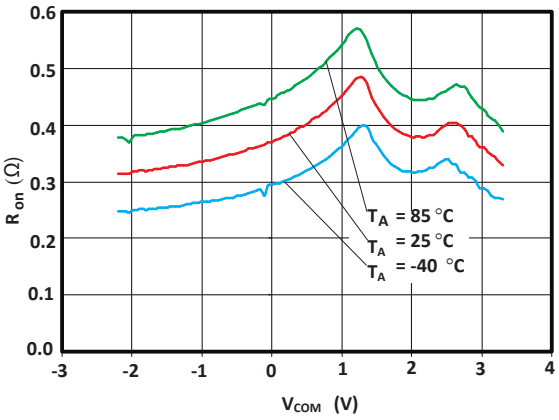


Figure 3. R_{on} vs V_{COM} (V_{CC} = 3.3 V)

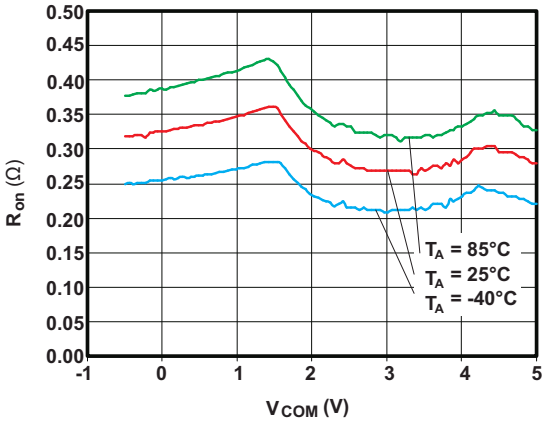


Figure 4. R_{on} vs V_{COM} (V_{CC} = 5 V)

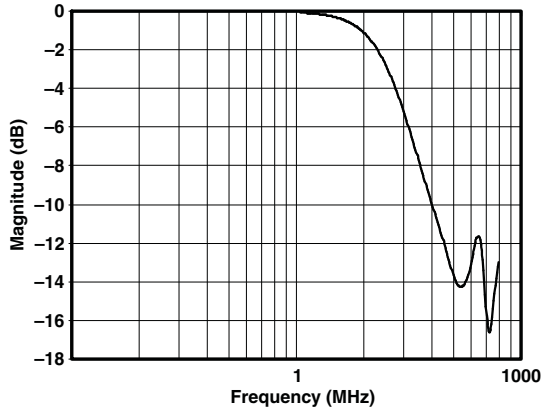


Figure 5. Insertion Loss

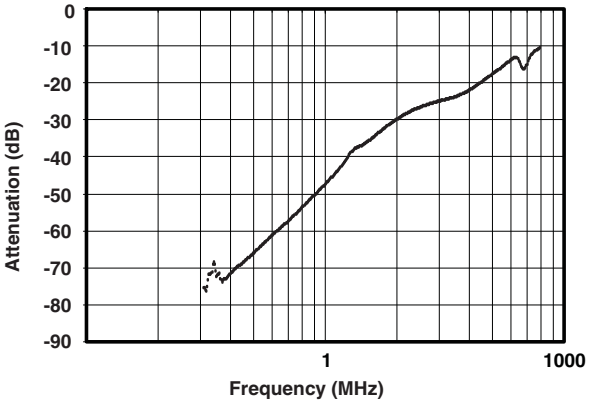


Figure 6. Off Isolation vs Frequency

Typical Characteristics (continued)

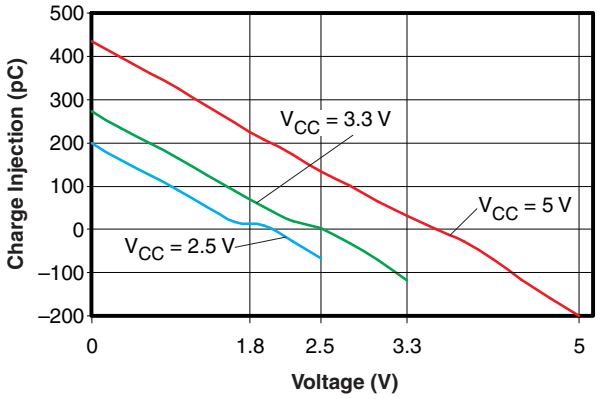


Figure 7. Charge Injection (Q_C) vs V_{COM}

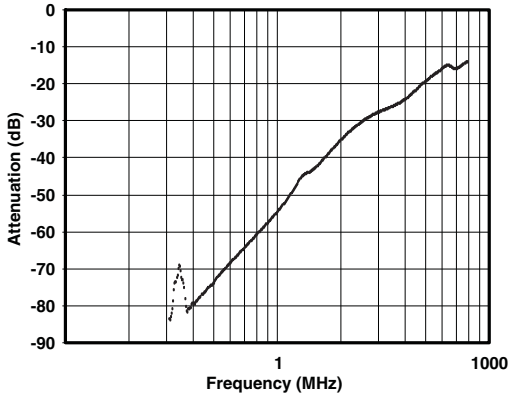


Figure 8. Crosstalk (V_{CC} = 3.3 V)

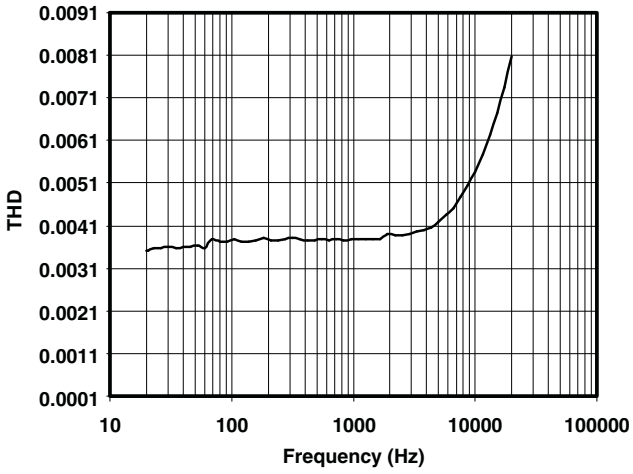


Figure 9. Total Harmonic Distortion vs Frequency

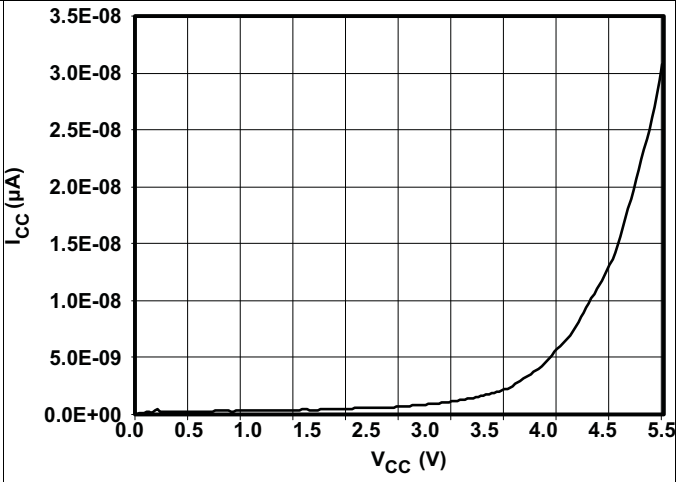


Figure 10. Power-Supply Current vs V_{CC}

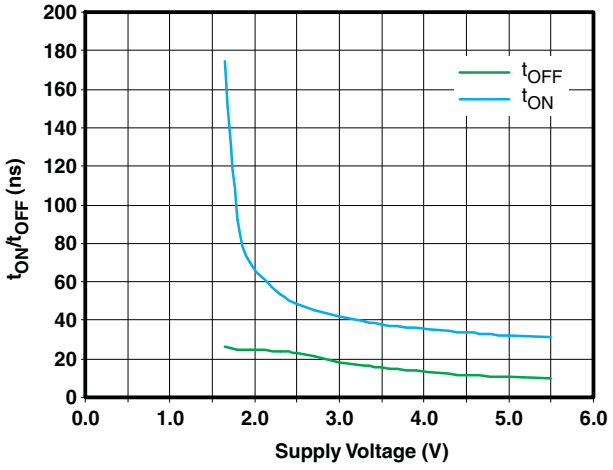


Figure 11. t_{ON} And t_{OFF} vs Supply Voltage

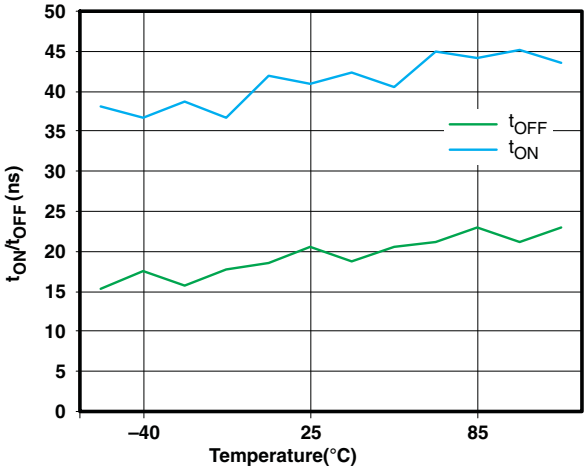


Figure 12. t_{ON} And t_{OFF} vs Temperature (2.5-V Supply)

7 Parameter Measurement Information

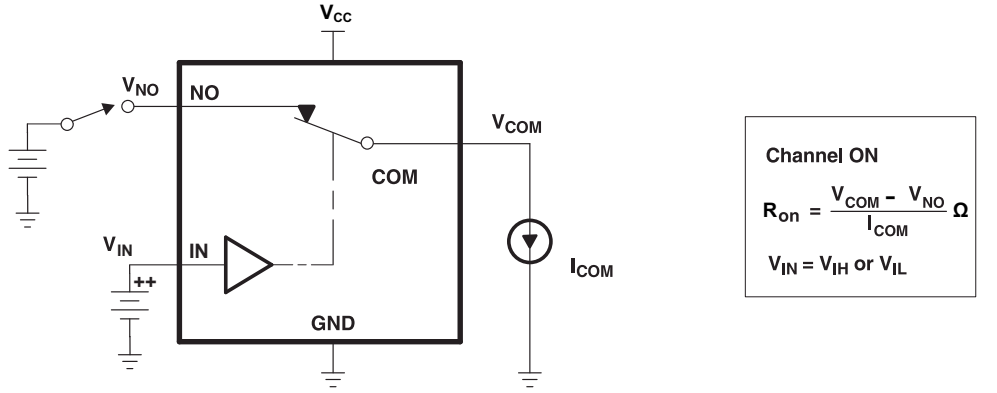


Figure 13. ON-state resistance (R_{on})

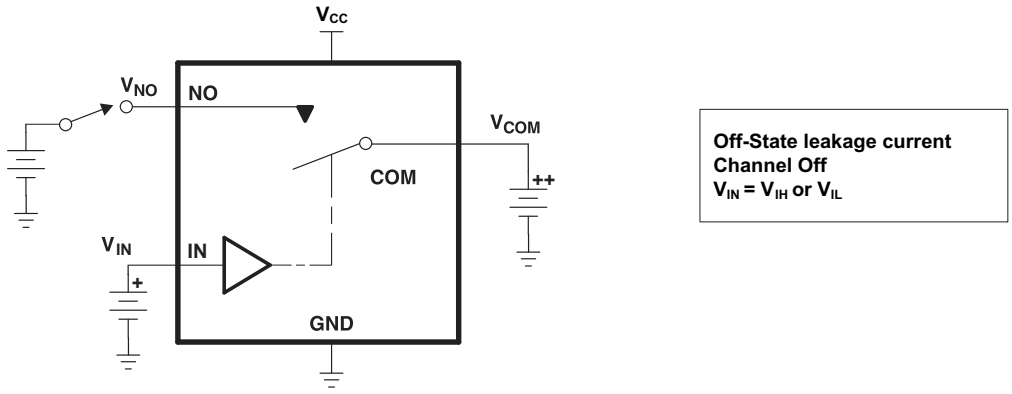


Figure 14. OFF-state leakage current ($I_{COM(OFF)}$, $I_{NO(OFF)}$)

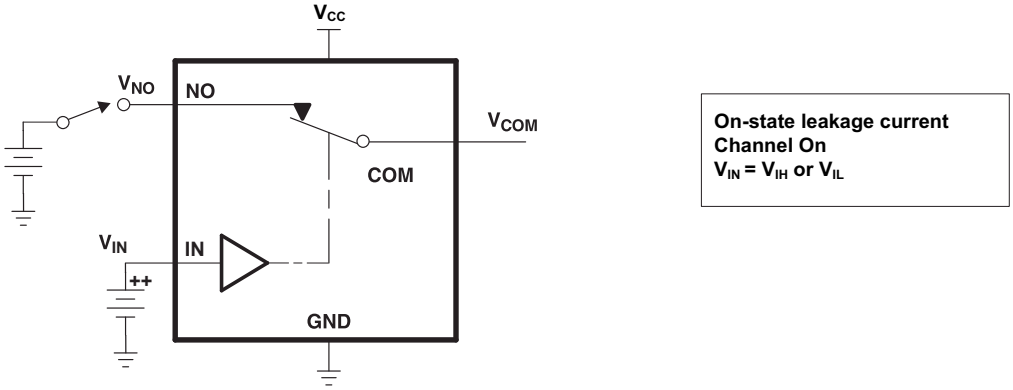


Figure 15. ON-state leakage current ($I_{COM(ON)}$, $I_{NO(ON)}$)

Parameter Measurement Information (continued)

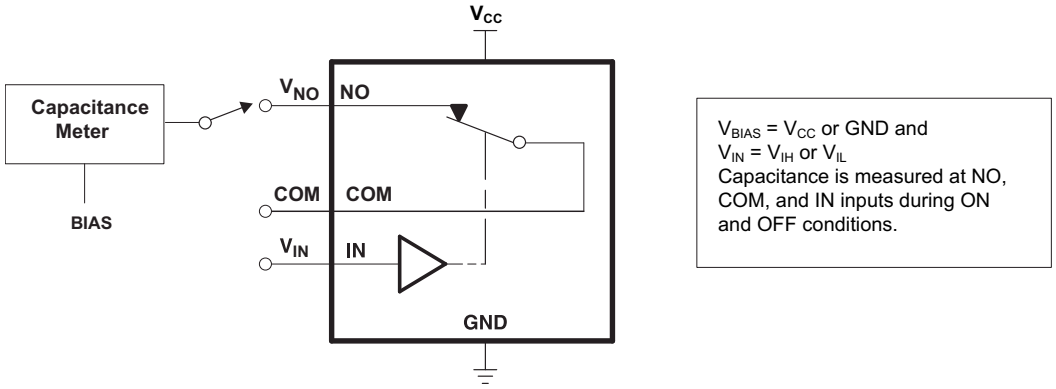
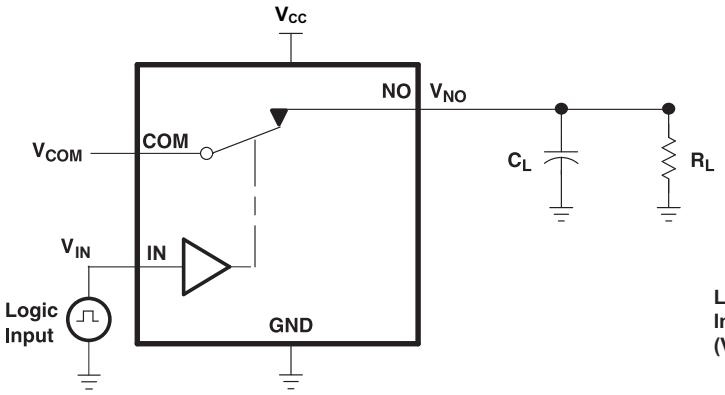
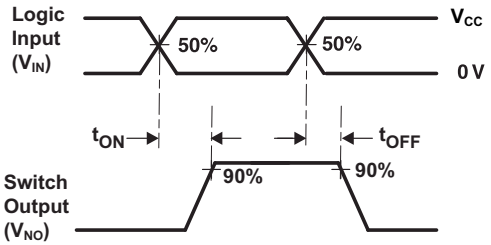


Figure 16. Capacitance
(C_I, $C_{COM(OFF)}$, $C_{COM(ON)}$, $C_{NO(OFF)}$, $C_{NO(ON)}$)



TEST	R_L	C_L	V_{COM}
t_{ON}	300 Ω	35 pF	V_{CC}
OFF	300 Ω	35 pF	V_{CC}

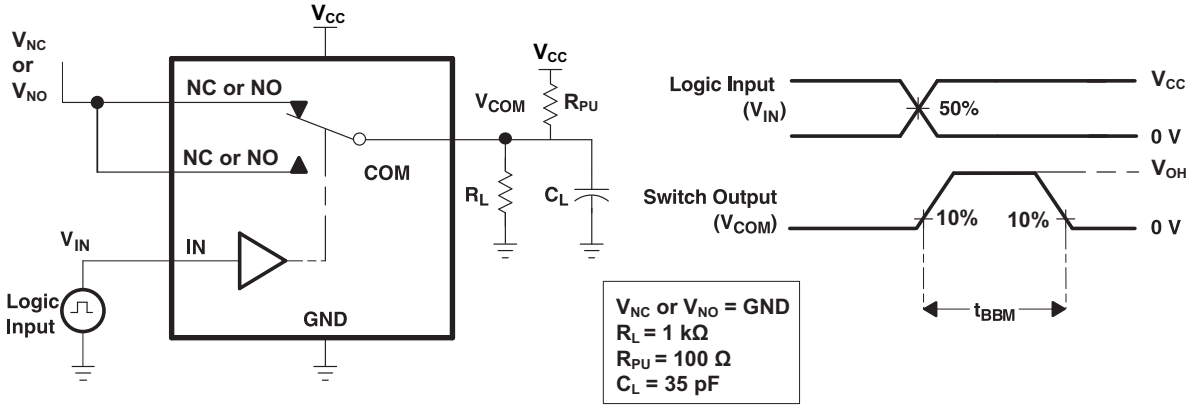


A. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r < 5 ns, t_f < 5 ns.

B. C_L includes probe and jig capacitance.

Figure 17. Turnon (t_{ON}) and Turnoff time (t_{OFF})

Parameter Measurement Information (continued)



A. C_L includes probe and jig capacitance.

B. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r < 5 ns, t_f < 5 ns.

Figure 18. Break-Before-Make Time (t_{BBM})

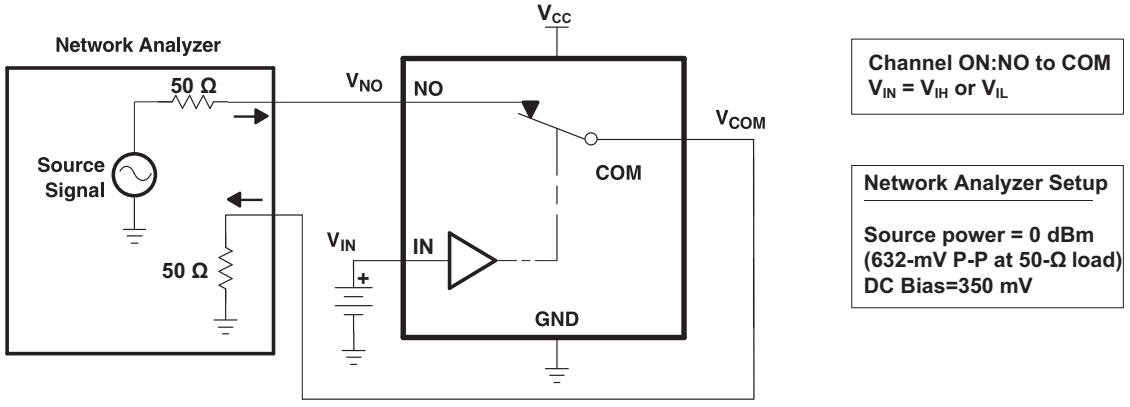


Figure 19. Bandwidth (BW)

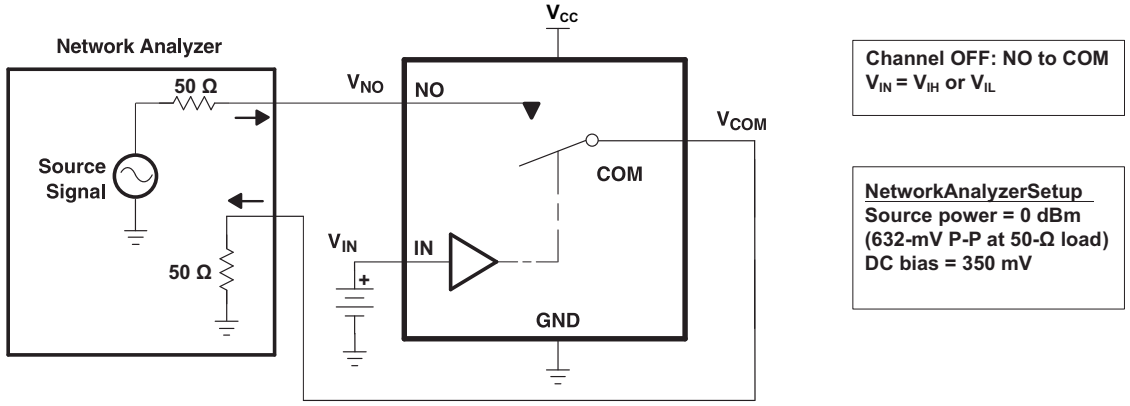


Figure 20. OFF isolation (O_{ISO})

Parameter Measurement Information (continued)

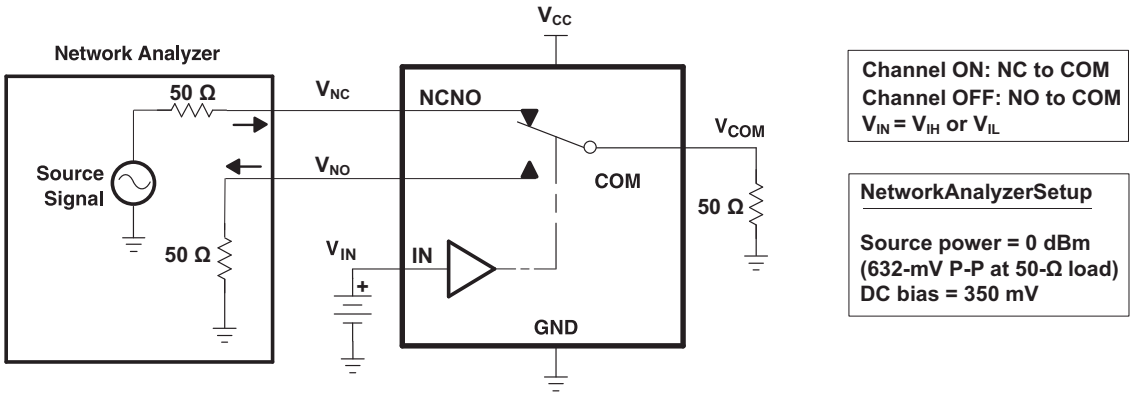
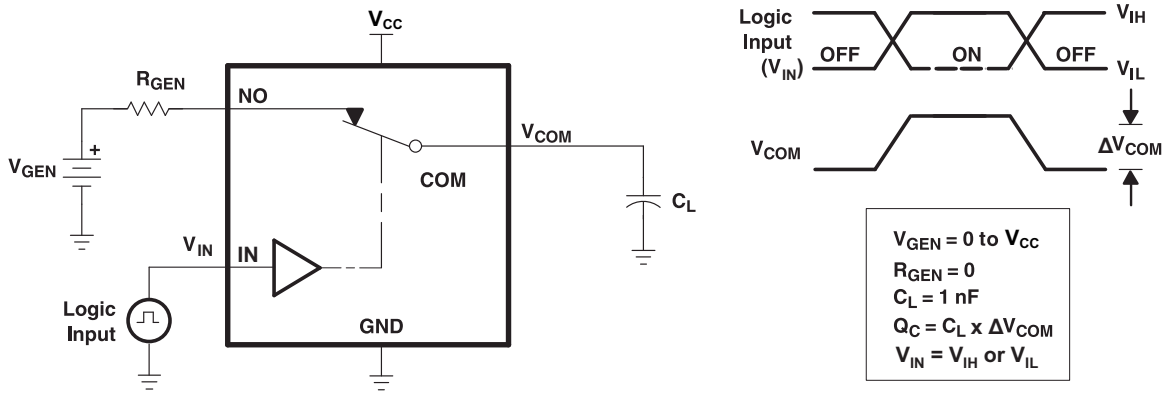


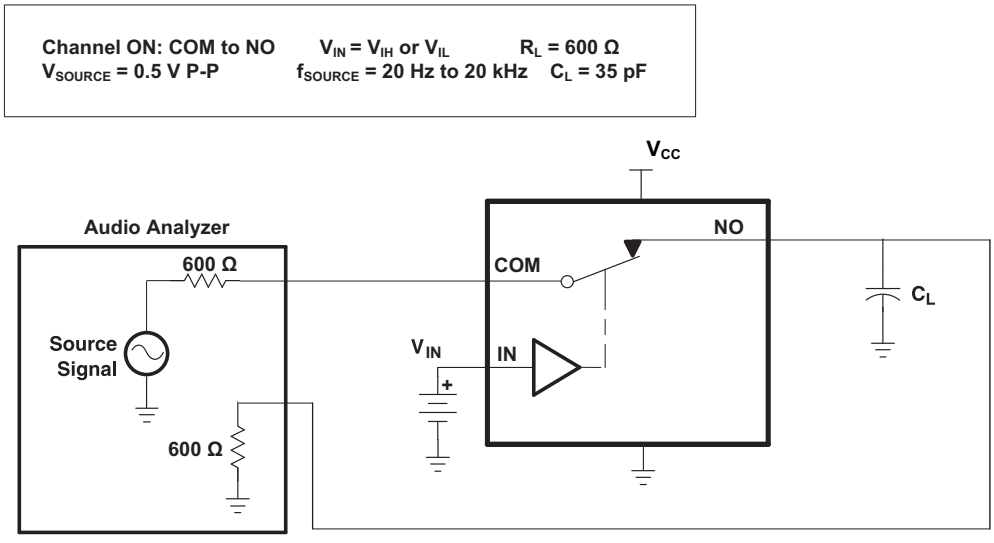
Figure 21. Crosstalk (X_{TALK})



A. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r < 5 ns, t_f < 5 ns.

B. C_L includes probe and jig capacitance.

Figure 22. Charge injection (Q_C)



A. C_L includes probe and jig capacitance.

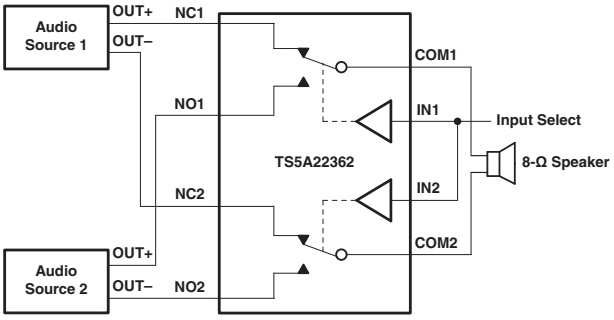
Figure 23. Total Harmonic Distortion (THD)

8 Detailed Description

8.1 Overview

The TS5A22362 is a bidirectional, 2-channel single-pole double-throw (SPDT) analog switches designed to operate from 2.3 V to 5.5 V. The devices feature negative signal capability that allows signals below ground to pass through the switch without distortion. The break-before-make feature prevents signal distortion during the transferring of a signal from one path to another. Low ON-state resistance, excellent channel-to-channel ON-state resistance matching, and minimal total harmonic distortion (THD) performance are ideal for audio applications

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Negative Signaling Capacity

The TS5A22362 dual SPDT switches feature negative signal capability that allows signals below ground to pass through without distortion. These analog switches operate from a single +2.3-V to +5.5-V supply. The input and output signal swing of the device is dependant of the supply voltage V_{CC}: the devices pass signals as high as V_{CC} and as low as V_{CC} – 5.5 V, including signals below ground with minimal distortion.

Table 1 shows the input/output signal swing the user can get with different supply voltages.

Table 1. Input/Output signal swing

SUPPLY VOLTAGE, V_{CC}	MINIMUM (V_{NC}, V_{NO}, V_{COM}) = V_{CC} – 5.5	MAXIMUM (V_{NC}, V_{NO}, V_{COM}) = V_{CC}
5.5 V	0 V	5.5 V
4.5 V	–1.9 V	4.5 V
3.6 V	–2.5 V	3.6 V
3.0 V	–2.5 V	3.0 V
2.7 V	–2.8 V	2.7 V
2.3 V	–3.2 V	2.3 V

8.4 Device Functional Modes

The function table for TS5A22362 is shown in Table 2

Table 2. Function Table

IN	NC TO COM, COM TO NC	NO TO COM, COM TO NO
L	ON	OFF
H	OFF	ON

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

Ensure that the device is powered up with a supply voltage on VCC before a voltage can be applied to the signal paths NC and NO.

Tie the digitally controlled inputs select pins IN1 and IN2 to V_{CC} or GND to avoid unwanted switch states that could result if the logic control pins are left floating.

All unused digital inputs of the device must be held at VCC or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, SCBA004.

9.2 Typical Application

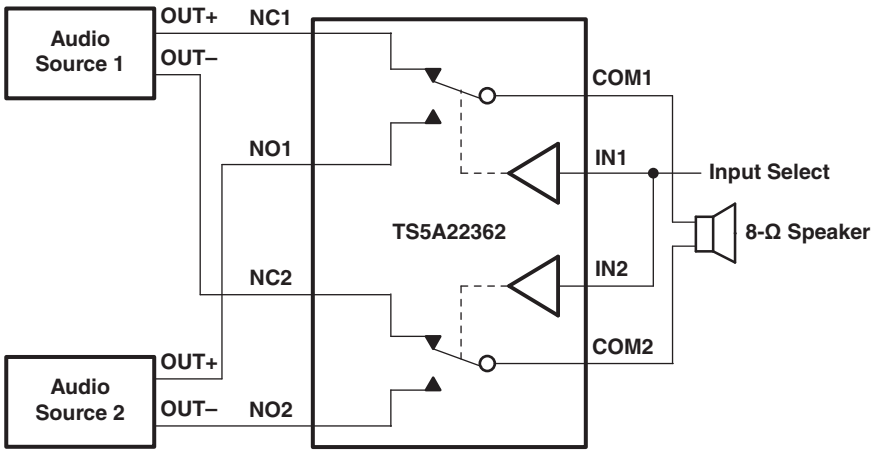


Figure 24. Typical Application

9.2.1 Design Requirements

Tie the digitally controlled inputs select pins IN1 and IN2 to V_{CC} or GND to avoid unwanted switch states that could result if the logic control pins are left floating.

9.2.2 Detailed Design Procedure

Select the appropriate supply voltage to cover the entire voltage swing of the signal passing through the switch because the TS5A22362 operates from a single +2.3-V to +5.5-V supply and the input/output signal swing of the device is dependant of the supply voltage V_{CC}. The device will pass signals as high as V_{CC} and as low as V_{CC} – 5.5 V. Use table 2 as a guide for selecting supply voltage based on the signal passing through the switch.

Ensure that the device is powered up with a supply voltage on VCC before a voltage can be applied to the signal paths NC and NO.

Typical Application (continued)

9.2.3 Application Curve

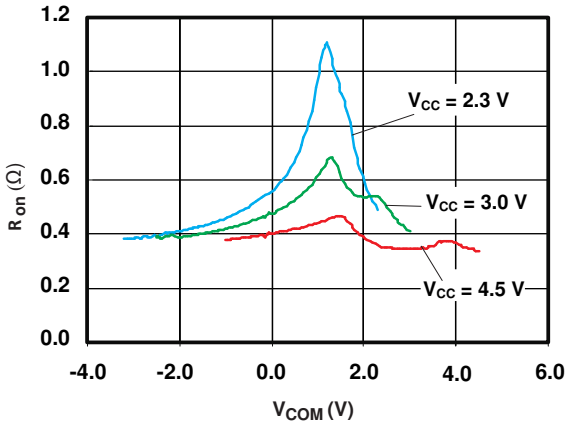


Figure 25. R_{on} vs V_{COM}

10 Power Supply Recommendations

The TS5A22362 operates from a single 2.3-V to 5.5-V supply. The device must be powered up with a supply voltage on VCC before a voltage can be applied to the signal paths NC and NO. It is recommended to include a 100-μs delay after VCC is at voltage before applying a signal on NC and NO paths

It is also good practice to place a 0.1-μF bypass capacitor on the supply pin VCC to GND to smooth out lower frequency noise to provide better load regulation across the frequency spectrum.

11 Layout

11.1 Layout Guidelines

TI recommends placing a bypass capacitor as close to the supply pin VCC as possible to help smooth out lower frequency noise to provide better load regulation across the frequency spectrum.

Minimize trace lengths and vias on the signal paths in order to preserve signal integrity.

11.2 Layout Example

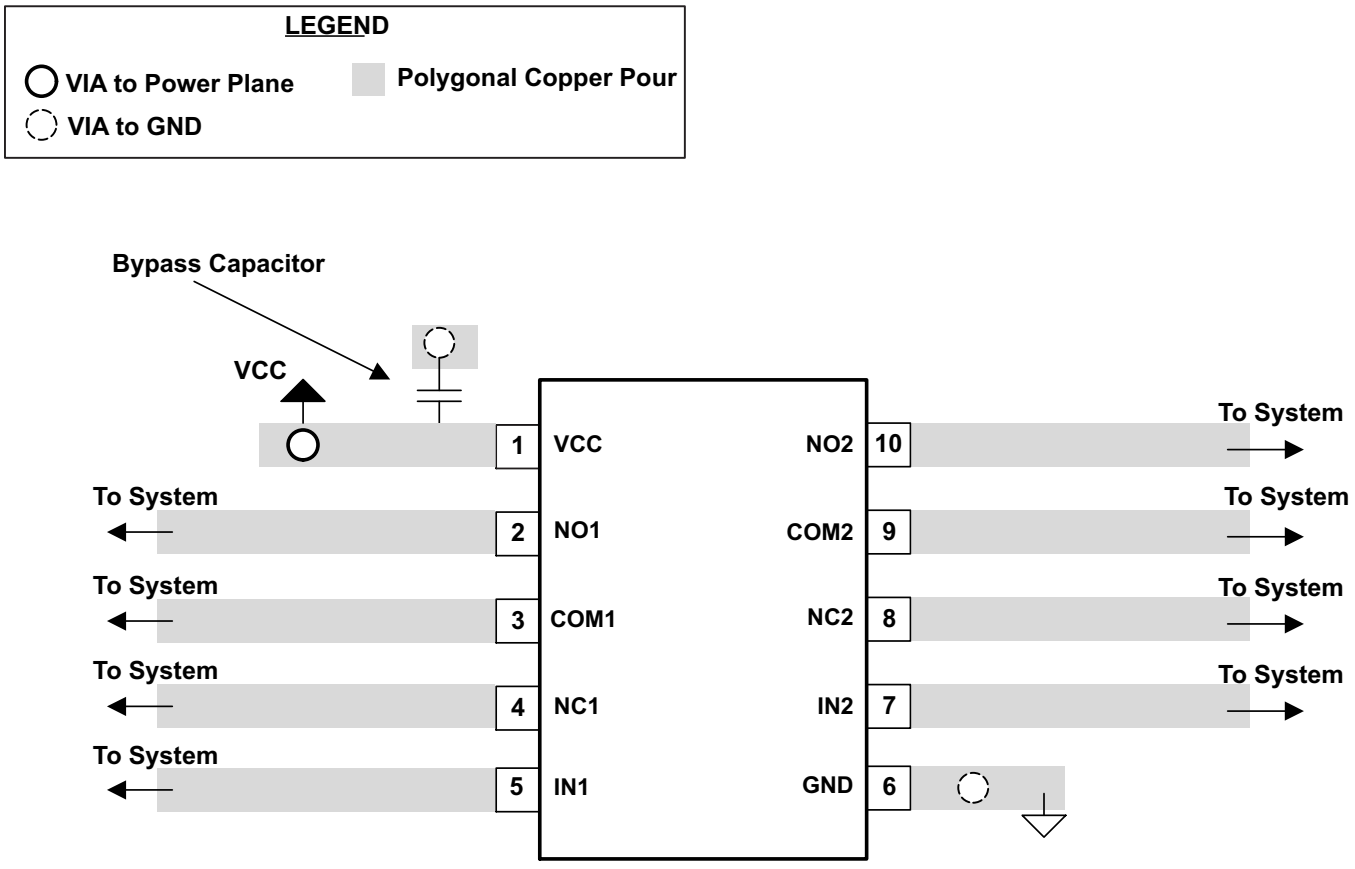


Figure 26. Layout example of TS5A22362

12 器件和文档支持

12.1 接收文档更新通知

要接收文档更新通知，请导航至 ti.com. 上的器件产品文件夹。单击右上角的*通知我*进行注册，即可每周接收产品信息更改摘要。有关更改的详细信息，请查看任何已修订文档中包含的修订历史记录。

12.2 社区资源

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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12.3 商标

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All other trademarks are the property of their respective owners.

12.4 静电放电警告

这些装置包含有限的内置 ESD 保护。 存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

12.5 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

13 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此数据表的浏览器版本，请查阅左侧的导航栏。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TS5A22362DGSR	ACTIVE	VSSOP	DGS	10	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	39R	Samples
TS5A22362DGSRG4	LIFEBUY	VSSOP	DGS	10	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	39R	
TS5A22362DRCR	ACTIVE	VSON	DRC	10	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	ZVG	Samples
TS5A22362DRCT-NM	LIFEBUY	VSON	DRC	10	250	RoHS & Green	SN	Level-2-260C-1 YEAR	-40 to 85	ZVGNM	
TS5A22362YZPR	ACTIVE	DSBGA	YZP	10	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	(39, 392)	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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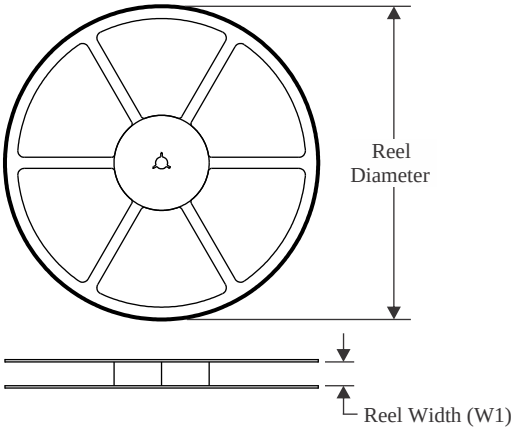
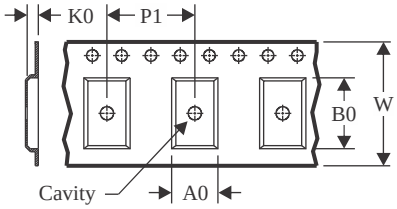
TAPE AND REEL INFORMATION

REEL DIMENSIONS

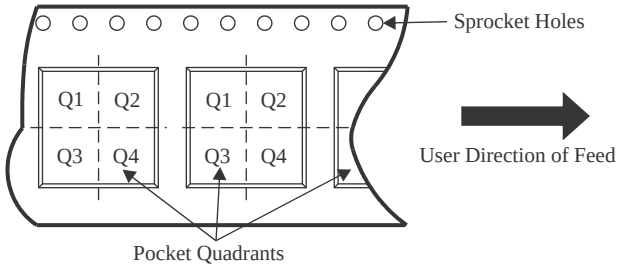


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

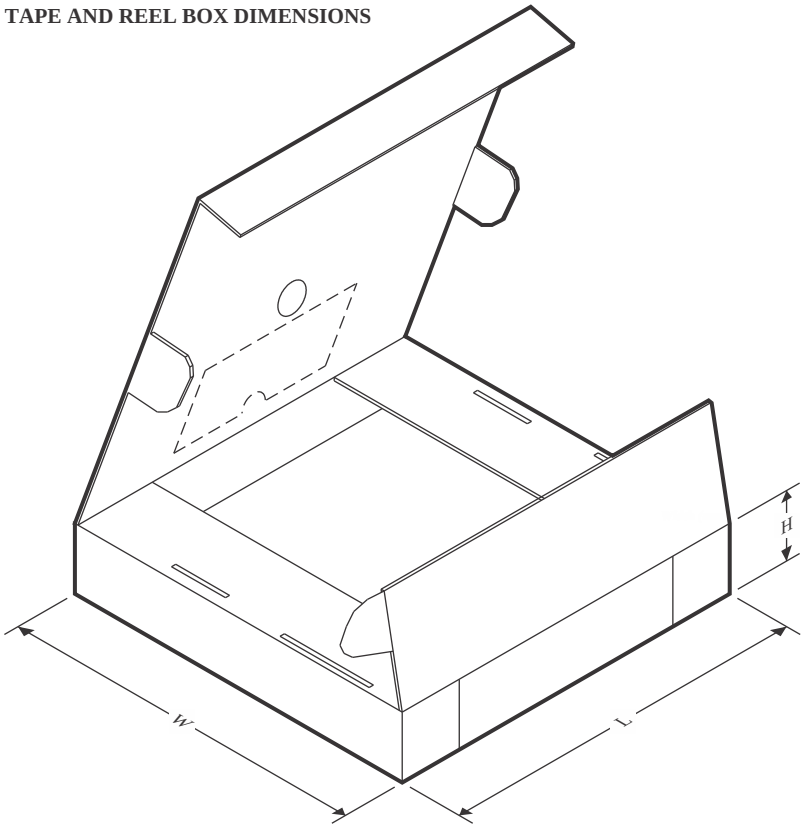
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TS5A22362DGSR	VSSOP	DGS	10	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TS5A22362DRCR	VSON	DRC	10	3000	330.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TS5A22362DRCT-NM	VSON	DRC	10	250	180.0	12.4	3.3	3.3	1.1	8.0	12.0	Q2
TS5A22362YZPR	DSBGA	YZP	10	3000	178.0	9.2	1.49	1.99	0.63	4.0	8.0	Q2

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

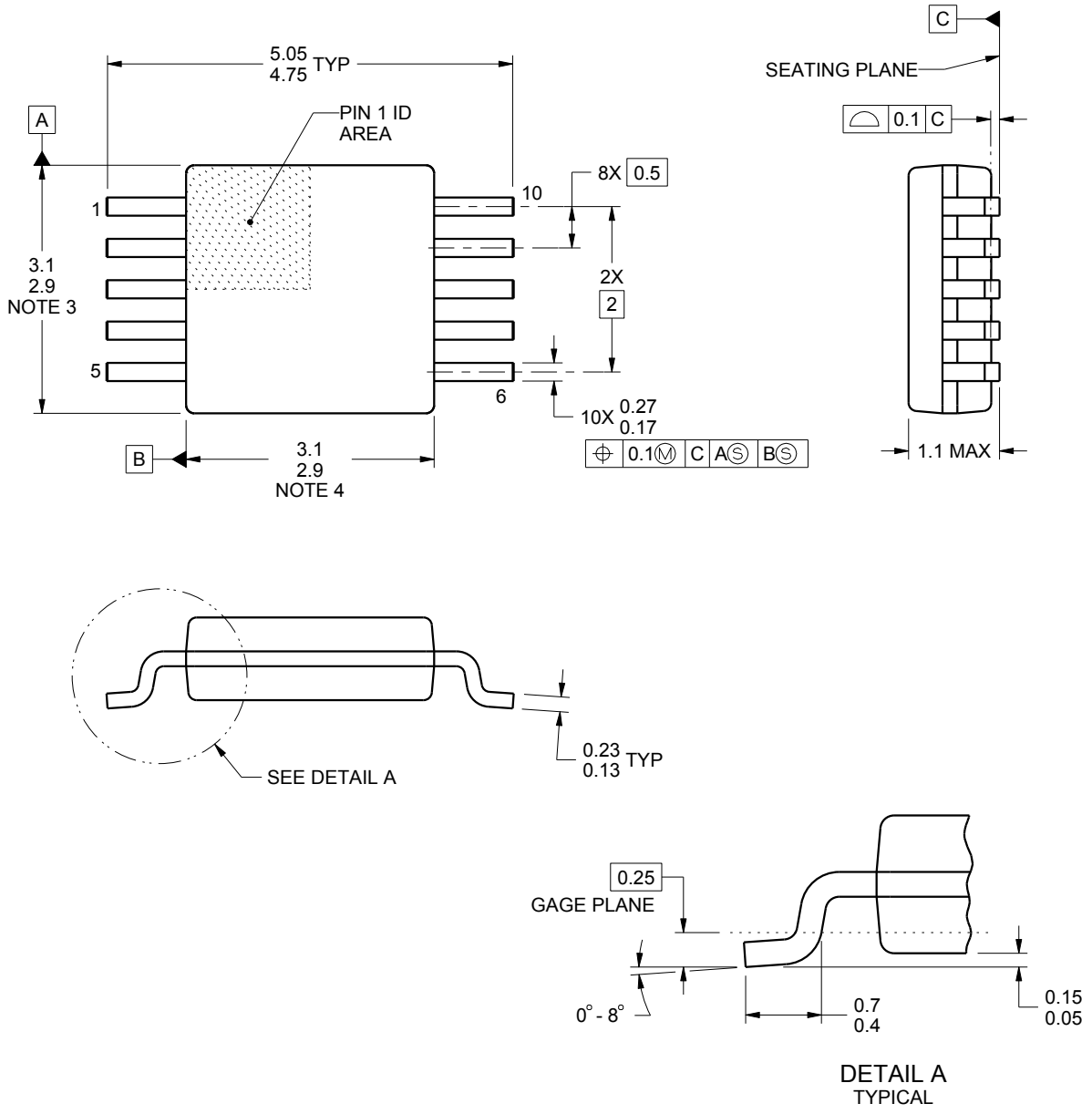
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TS5A22362DGSR	VSSOP	DGS	10	2500	358.0	335.0	35.0
TS5A22362DRCR	VSON	DRC	10	3000	356.0	356.0	35.0
TS5A22362DRCT-NM	VSON	DRC	10	250	210.0	185.0	35.0
TS5A22362YZPR	DSBGA	YZP	10	3000	220.0	220.0	35.0

PACKAGE OUTLINE

DGS0010A

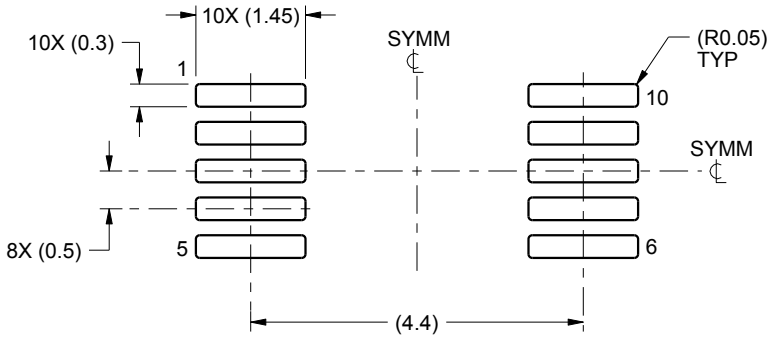
VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE

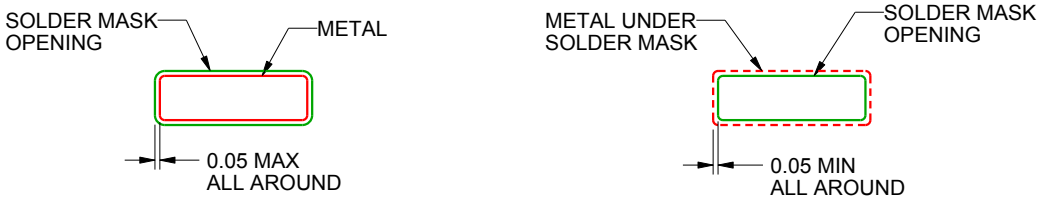


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-187, variation BA.



LAND PATTERN EXAMPLE
SCALE:10X

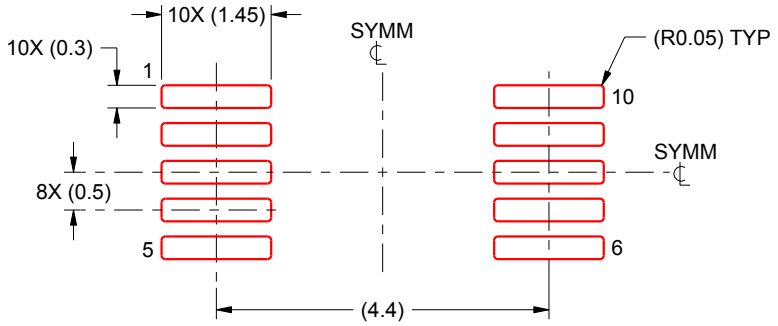


SOLDER MASK DETAILS
NOT TO SCALE

4221984/A 05/2015

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:10X

4221984/A 05/2015

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

GENERIC PACKAGE VIEW

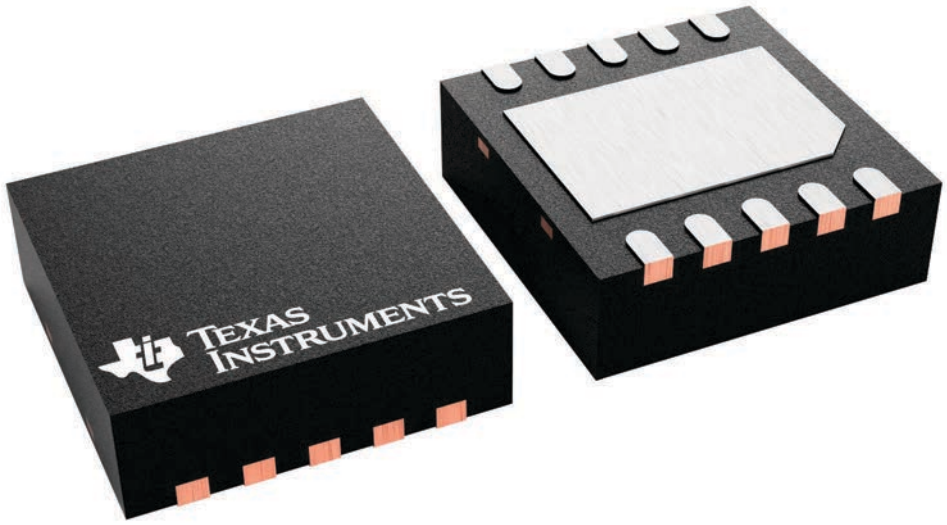
DRC 10

VSON - 1 mm max height

3 x 3, 0.5 mm pitch

PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



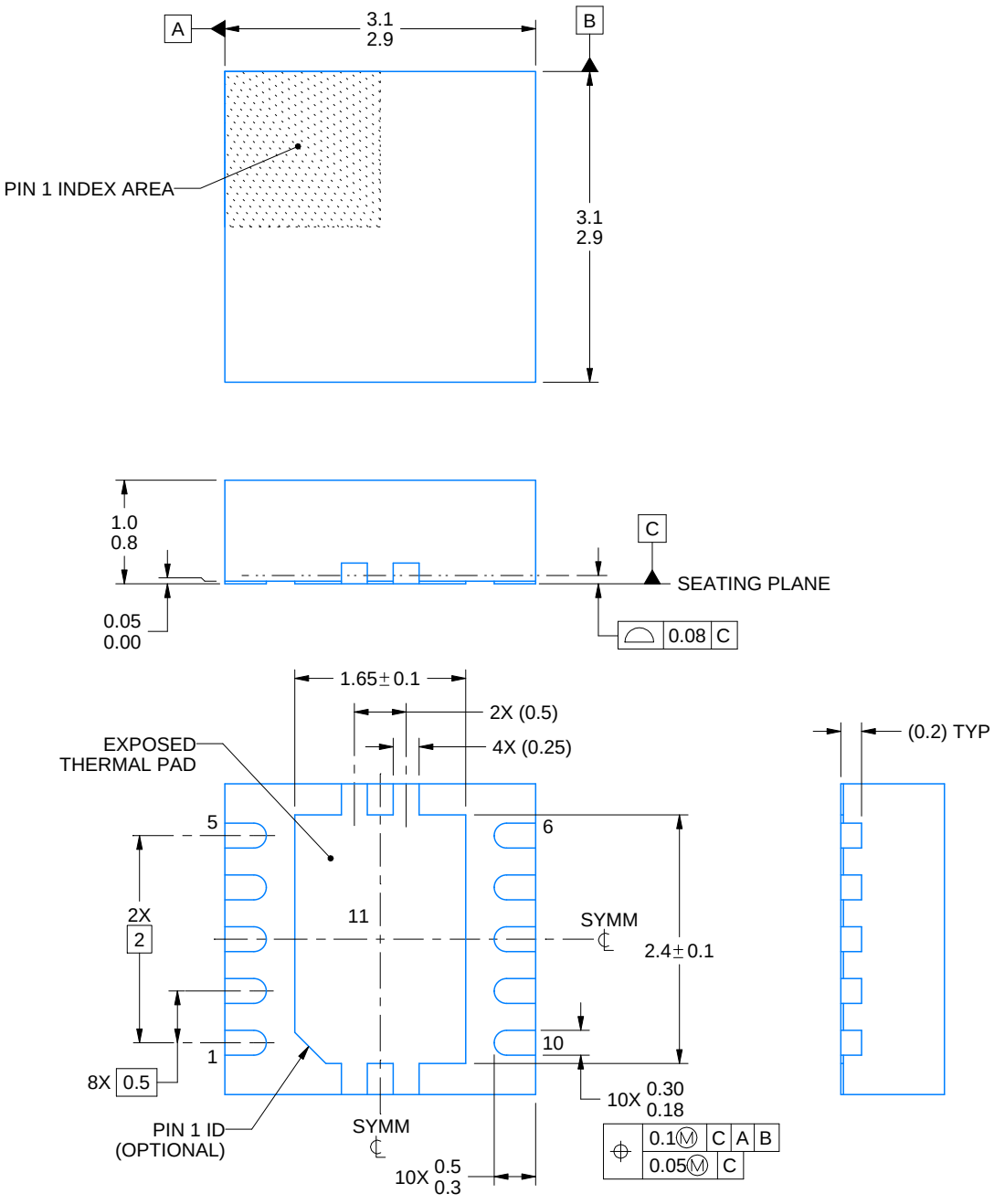
4226193/A

DRC0010J

PACKAGE OUTLINE

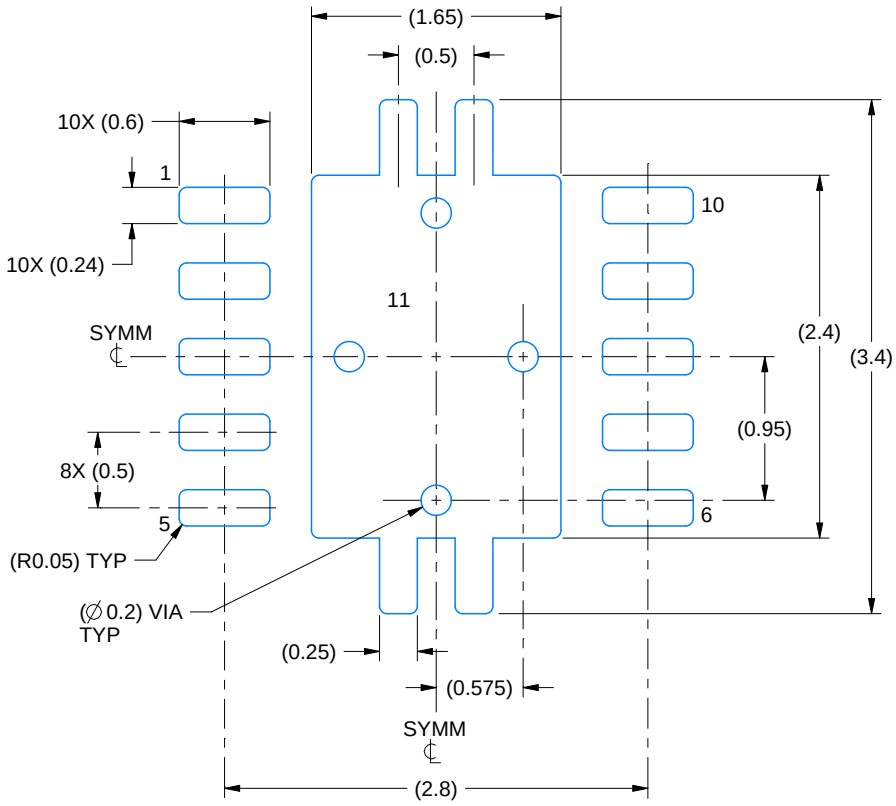
VSON - 1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD

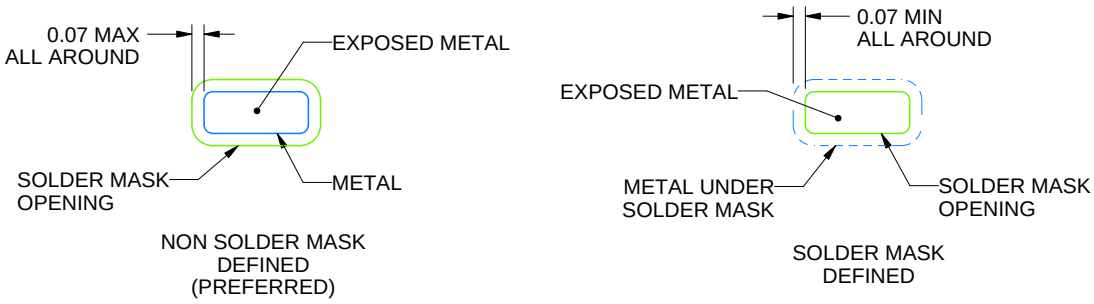


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:20X



SOLDER MASK DETAILS

4218878/B 07/2018

NOTES: (continued)

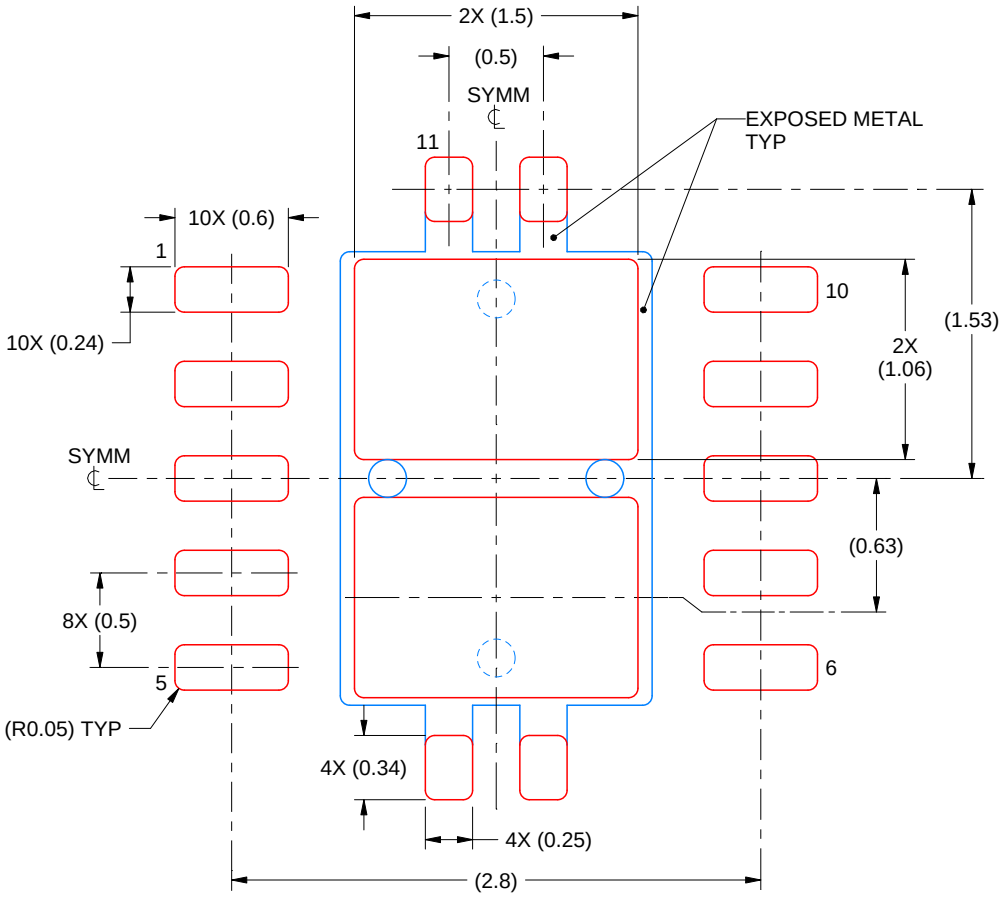
4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

EXAMPLE STENCIL DESIGN

DRC0010J

VSON - 1 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

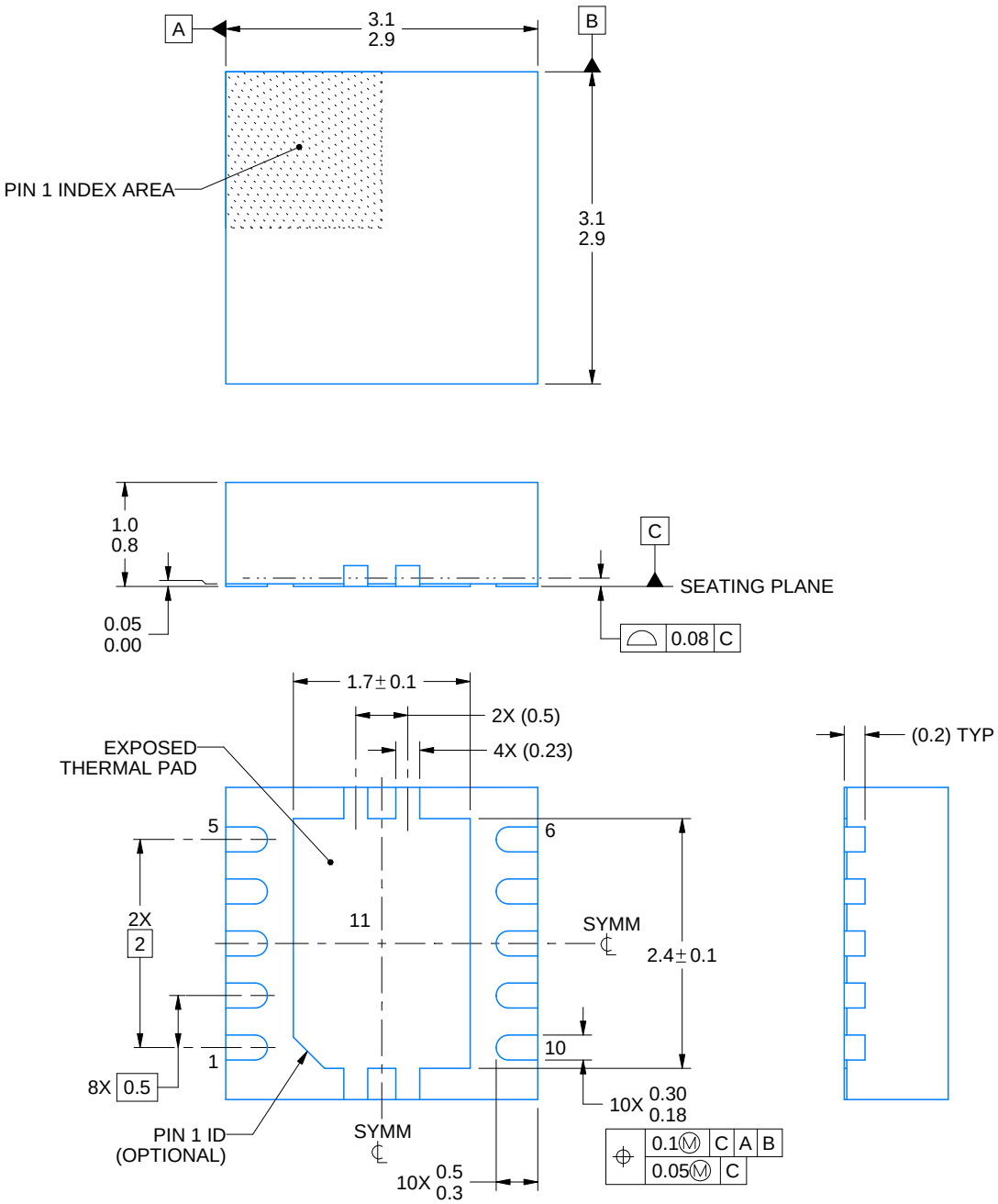
EXPOSED PAD 11:
80% PRINTED SOLDER COVERAGE BY AREA
SCALE:25X

4218878/B 07/2018

NOTES: (continued)

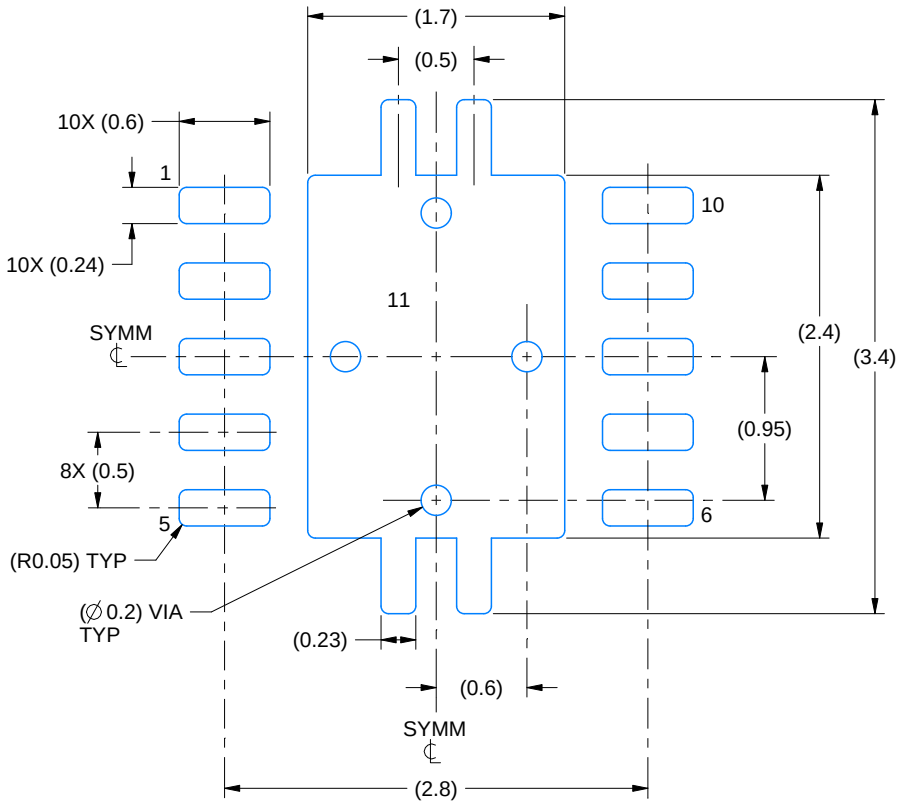
6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

PLASTIC SMALL OUTLINE - NO LEAD

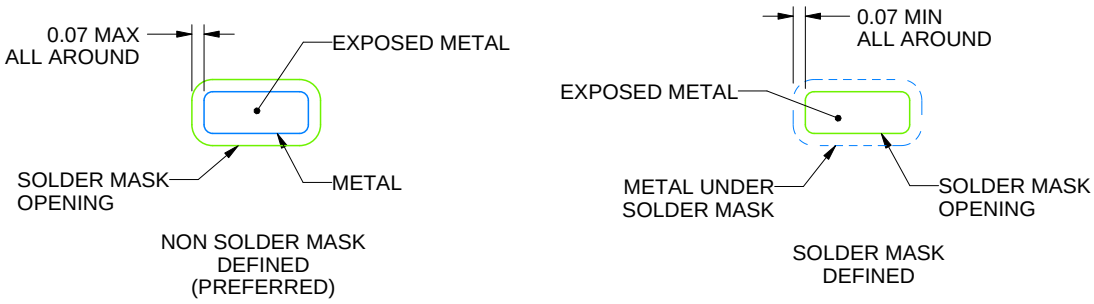


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:20X

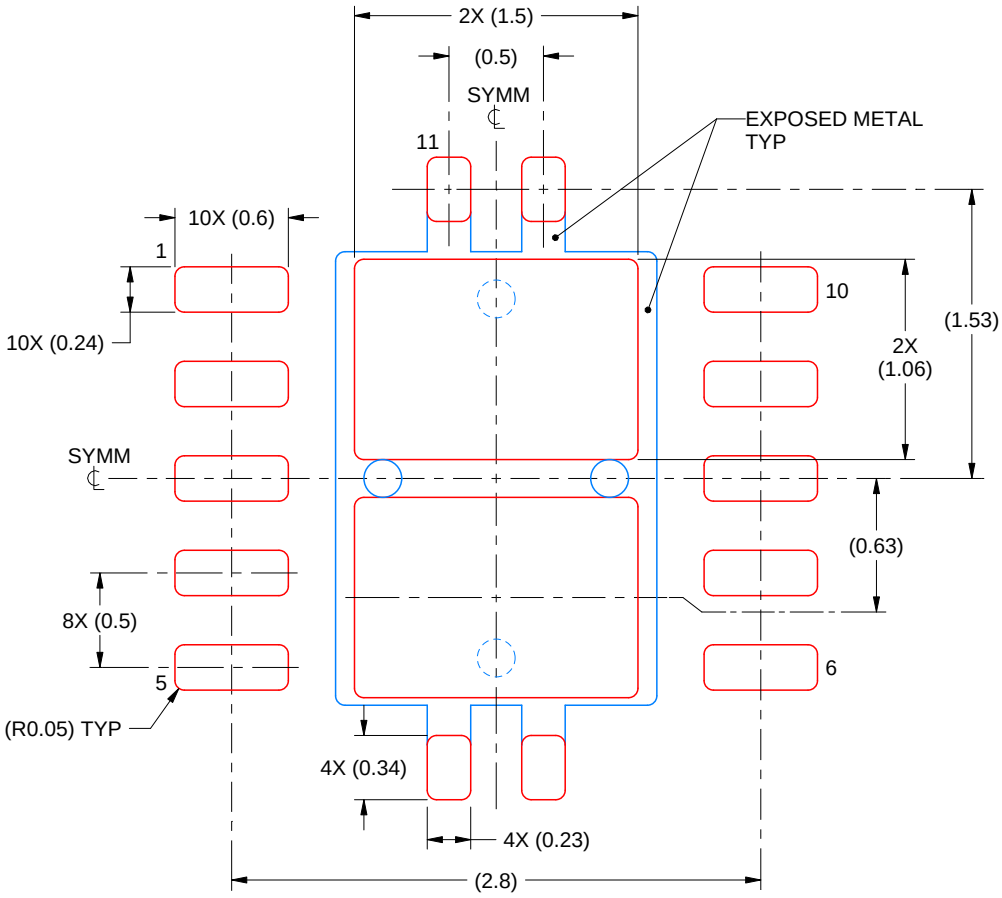


SOLDER MASK DETAILS

4218883/A 12/2021

NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



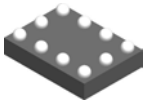
SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD 11:
80% PRINTED SOLDER COVERAGE BY AREA
SCALE:25X

4218883/A 12/2021

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

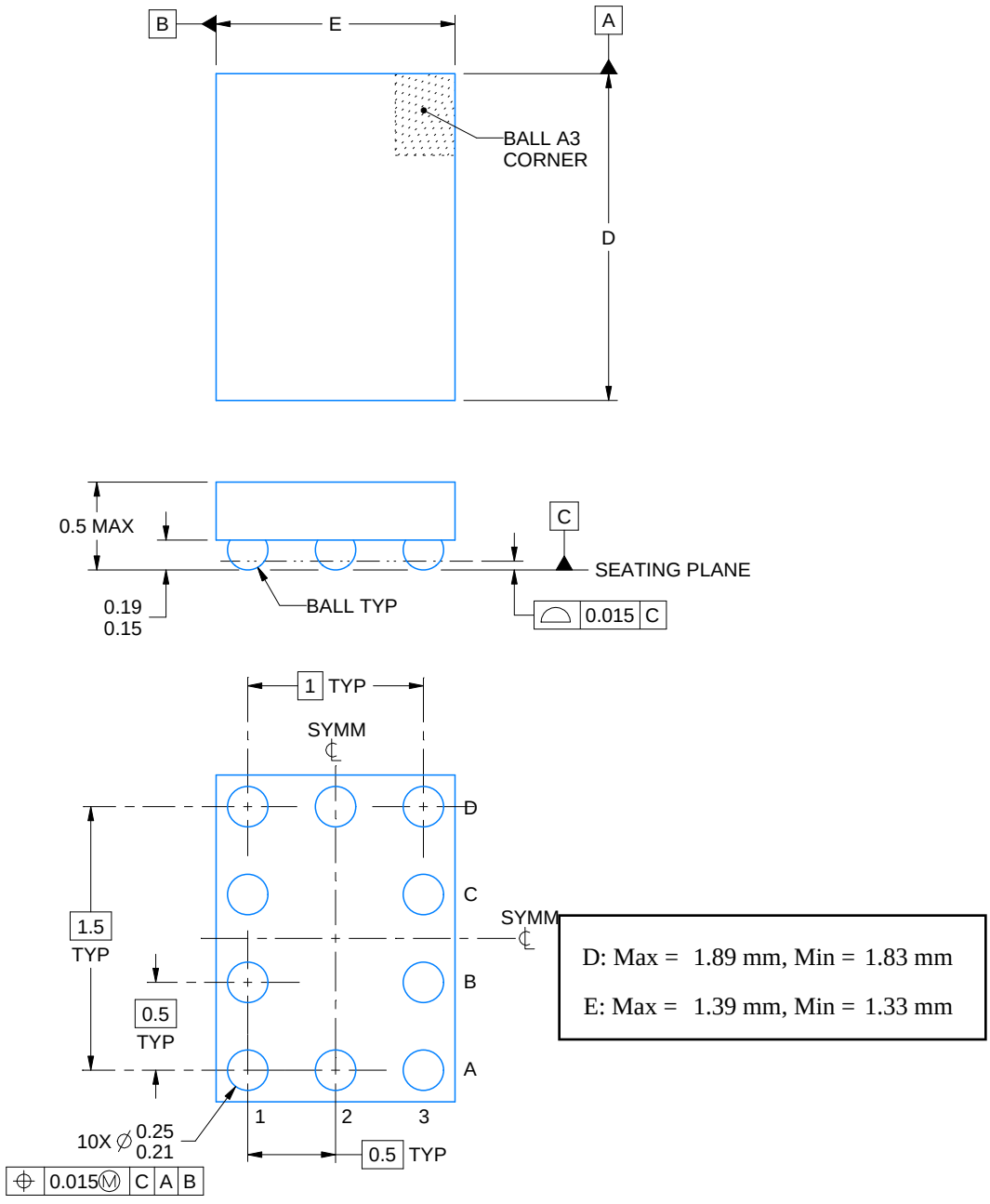


PACKAGE OUTLINE

YZP0010

DSBGA - 0.5 mm max height

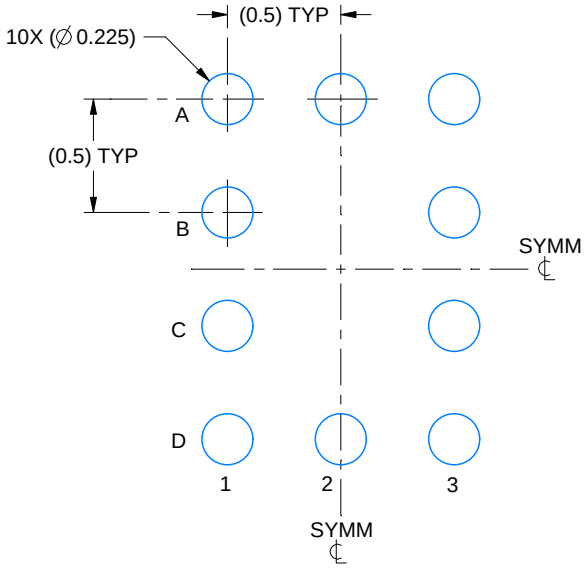
DIE SIZE BALL GRID ARRAY



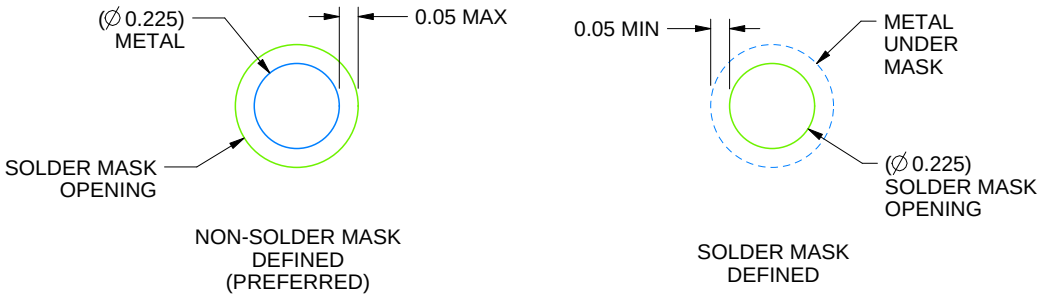
4219350/B 11/2017

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.



LAND PATTERN EXAMPLE
SCALE:30X



SOLDER MASK DETAILS
NOT TO SCALE

4219350/B 11/2017

NOTES: (continued)

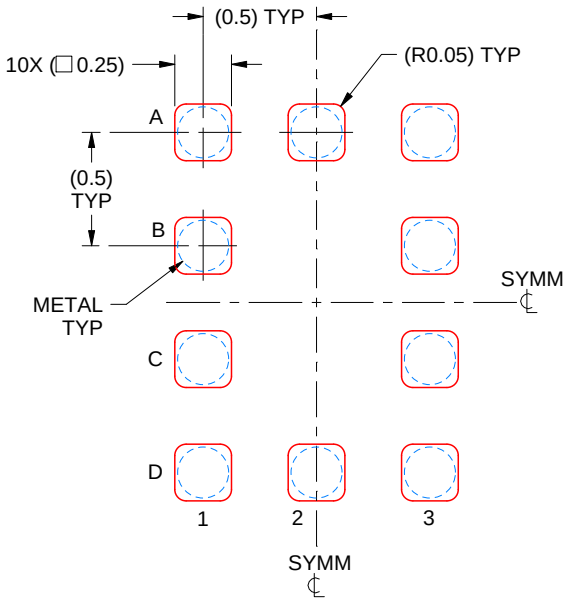
3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints.
For more information, see Texas Instruments literature number SBVA017 (www.ti.com/lit/sbva017).

EXAMPLE STENCIL DESIGN

YZP0010

DSBGA - 0.5 mm max height

DIE SIZE BALL GRID ARRAY



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:30X

4219350/B 11/2017

NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

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